7MBR100XNA065-50

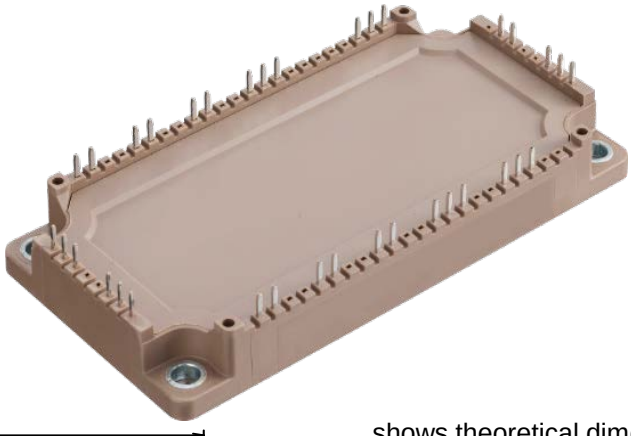
IGBT Modules

Power Module(X series)
650V / 100A / PIM

□ Feactures

Low $V_{CE(sat)}$
Compact Package
P.C.Board Mount Module
Converter Diode Bridge Dynamic Brake Circuit
RoHS compliant Product

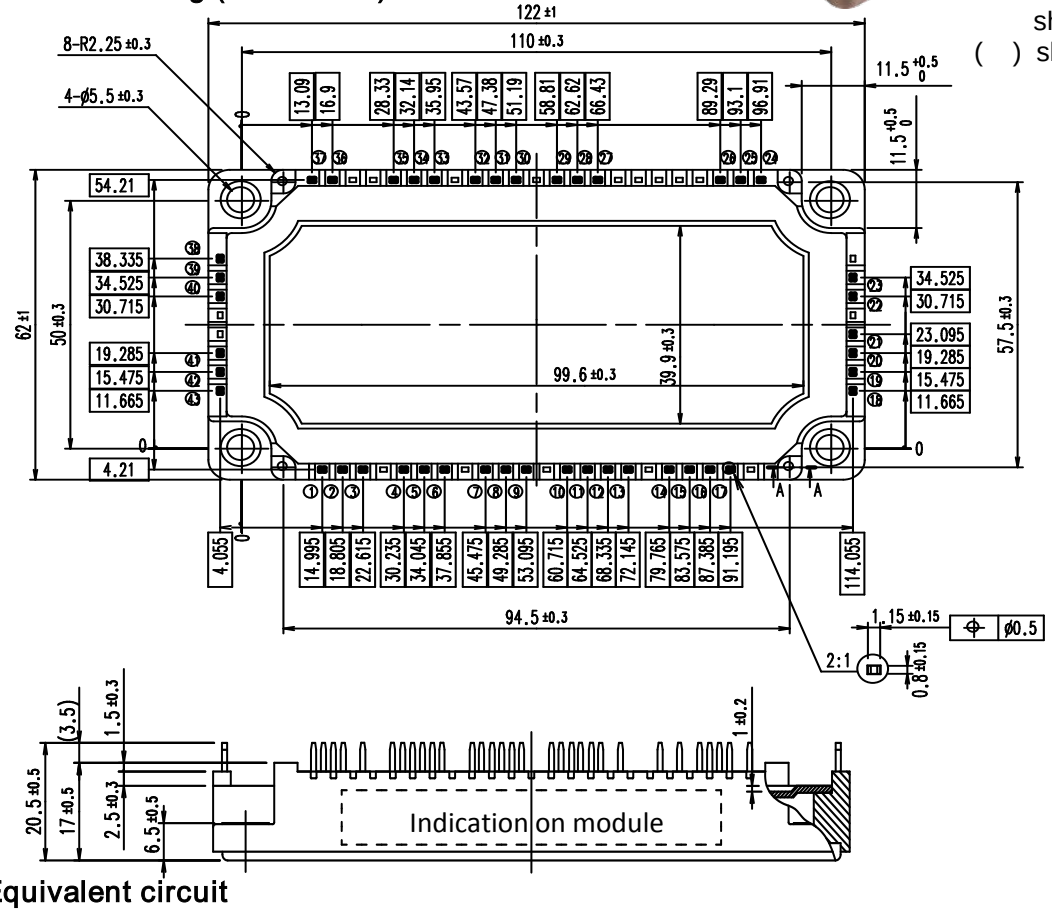
□ Typical appearance



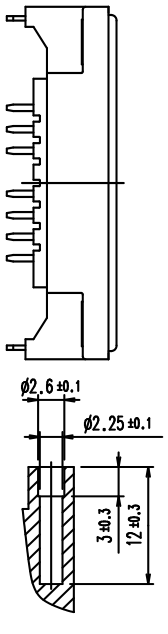
□Applications

Inverter for Motor Drive
AC and DC Servo Drive Amplifier
Uniterruptible Power Supply

□ Outline drawing (Unit : mm)

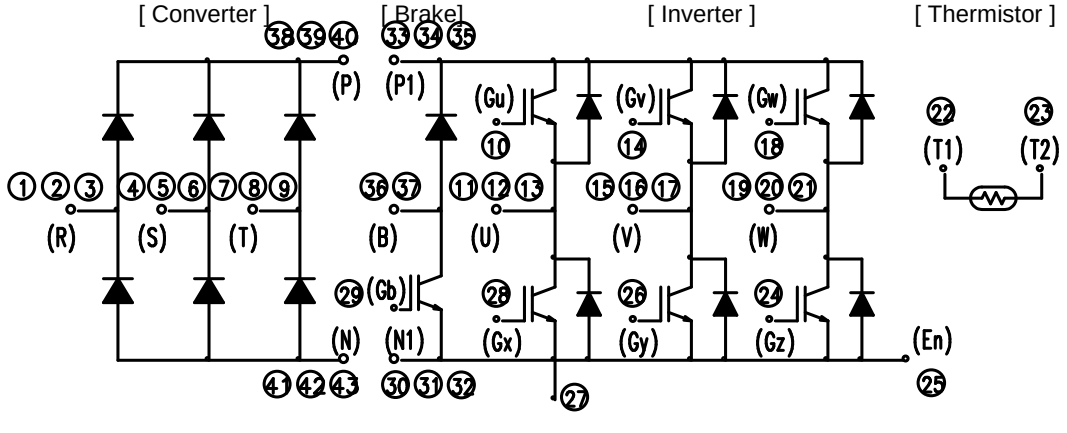


shows theoretical dimension.
( ) shows reference dimension.



Weight: 310 g (typ.)

□ Equivalent circuit



□ Maximum ratings (at T_c = 25°C unless otherwise specified)

	Items		Symbols	Conditions		Maximum ratings	Units
Inverter	Collector-Emitter voltage		V_{CES}			650	V
	Gate-Emitter voltage		V_{GES}			±20	V
	Collector current		I_C	Continuous	T_c=80°C	100	A
			I_C pulse	1ms		200	
	Forward current		I_F	Continuous		100	
			I_F pulse	1ms		200	
	Collector power dissipation		P_C	1 device		330	W
Brake IGBT	Collector-Emitter voltage		V_{CES}			650	V
	Gate-Emitter voltage		V_{GES}			±20	V
	Collector current		I_C	Continuous	T_c=80°C	50	A
			I_C pulse	1ms		100	
	Collector power dissipation		P_C	1 device		210	W
Brake FWD	Forward current		I_F	Continuous		30	A
			I_{FRM}	1ms		60	
	Repetitive peak reverse voltage		V_{RRM}			650	V
Converter	Repetitive peak reverse voltage		V_{RRM}			800	V
	Average output current		I_O	Three-phase full wave rectified current	T_c=80°C	100	A
	Surge current (Non-Repetitive) (*1)		I_{FSM}	t=10ms, Half sine wave form	T_{vj}=25°C	850	A
					T_{vj}=150°C	745	
	I^2t (Non-Repetitive) (*1)		I^2t		T_{vj}=25°C	3640	A^2s
					T_{vj}=150°C	2800	
Junction temperature			T_{vj}	Inverter, Brake		175	°C
				Converter		150	
Operating junction temperature (under switching conditions)			T_{vjop}	Inverter, Brake		175	
				Converter		150	
Case temperature			T_c			125	
Storage temperature			T_{stg}			-40 ~ 125	
Isolation voltage		between terminals and copper base (*2)	V_{iso}	A.C. : 1min.		2500	Vrms
		between thermistor and others (*3)					
Screw torque (*4)		Mounting	-	M5		6.0	N·m

(*1) T_{vj} : Temperature at test start.

(*2) All terminals should be connected together during the test.

(*3) Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test.

(*4) Recommendable value : Mounting 2.5 ~ 6.0 N·m (M5)

□ Electrical characteristics (at T_{vj} = 25°C unless otherwise specified)

	Items	Symbols	Conditions		Characteristics min.	Characteristics typ.	Characteristics max.	Units
Inverter	Zero Gate voltage collector current	I_{CES}	V_{GE} = 0V V_{CE} = 650V		-	-	50	μA
	Gate-Emitter leakage current	I_{GES}	V_{CE} = 0V V_{GE} = +20/-20V		-	-	100	nA
	Gate-Emitter threshold voltage	$V_{GE(th)}$	V_{CE} = 20V I_C = 100mA		6.0	6.5	7.0	V
	Collector-Emitter saturation voltage	$V_{CE(sat)}$ (terminal)	V_{GE} = 15V I_C = 100A	T_{vj}=25°C	-	1.55	2.05	V
		$V_{CE(sat)}$ (chip)		T_{vj}=25°C	-	1.30	1.75	
				T_{vj}=125°C	-	1.45	-	
				T_{vj}=150°C	-	1.50	-	
				T_{vj}=175°C	-	1.55	-	
	Internal Gate resistance	r_g	-		-	6.75	-	Ω
	Capacitance	C_{ies}	V_{CE} = 10V, V_{GE} =0V, f = 1MHz		-	11.5	-	nF
		C_{oes}			-	0.44	-	
		C_{res}			-	0.16	-	
	Gate charge	Q_G	V_{CC} = 300V V_{GE}=-15 → +15V I_C = 100A		-	840	-	nC
	Forward voltage	V_F (terminal)	I_F = 100A	T_{vj}=25°C	-	1.80	2.30	V
		V_F (chip)		T_{vj}=25°C	-	1.55	2.00	
				T_{vj}=125°C	-	1.50	-	
				T_{vj}=150°C	-	1.50	-	
				T_{vj}=175°C	-	1.45	-	
	Switching time (*1)	$t_{d(on)}$	V_{CC} = 300V I_C,I_F = 100A L_s = 30nH V_{GE} = +15/-15 V R_G = 27 Ω	T_{vj}=25°C	-	0.48	-	μs
				T_{vj}=125°C	-	0.48	-	
				T_{vj}=150°C	-	0.49	-	
				T_{vj}=175°C	-	0.50	-	
		t_r	V_{CC} = 300V I_C,I_F = 100A L_s = 30nH V_{GE} = +15/-15 V R_G = 27 Ω	T_{vj}=25°C	-	0.12	-	
				T_{vj}=125°C	-	0.14	-	
				T_{vj}=150°C	-	0.15	-	
				T_{vj}=175°C	-	0.16	-	
		$t_{d(off)}$	V_{CC} = 300V I_C,I_F = 100A L_s = 30nH V_{GE} = +15/-15 V R_G = 27 Ω	T_{vj}=25°C	-	0.52	-	
				T_{vj}=125°C	-	0.55	-	
				T_{vj}=150°C	-	0.56	-	
				T_{vj}=175°C	-	0.57	-	
		t_f	V_{CC} = 300V I_C,I_F = 100A L_s = 30nH V_{GE} = +15/-15 V R_G = 27 Ω	T_{vj}=25°C	-	0.04	-	
				T_{vj}=125°C	-	0.05	-	
				T_{vj}=150°C	-	0.05	-	
				T_{vj}=175°C	-	0.05	-	
	Reverse recovery time	t_{rr}	V_{CC} = 300V I_C,I_F = 100A L_s = 30nH V_{GE} = +15/-15 V R_G = 27 Ω	T_{vj}=25°C	-	0.10	-	
				T_{vj}=125°C	-	0.24	-	
				T_{vj}=150°C	-	0.28	-	
				T_{vj}=175°C	-	0.30	-	

(*1) Turn on time (t_{on}) = $t_{d(on)}$ + t_r , Turn off time (t_{off}) = $t_{d(off)}$ + t_f

	Items	Symbols	Conditions		Characteristics min.	Characteristics typ.	Characteristics max.	Units
Inverter	Switching loss (per pulse)	E_{on}	V_{CC} = 300V, I_C,I_F = 100A, L_s = 30nH, V_{GE} = +15/-15 V, R_G = 27 Ω	T_{Vj}=25°C	-	4.35	-	mJ
				T_{Vj}=125°C	-	6.31	-	
				T_{Vj}=150°C	-	6.79	-	
				T_{Vj}=175°C	-	7.40	-	
		E_{off}	V_{CC} = 300V, I_C,I_F = 100A, L_s = 30nH, V_{GE} = +15/-15 V, R_G = 27 Ω	T_{Vj}=25°C	-	3.34	-	
				T_{Vj}=125°C	-	4.20	-	
				T_{Vj}=150°C	-	4.48	-	
				T_{Vj}=175°C	-	4.73	-	
		E_{rr}	V_{CC} = 300V, I_C,I_F = 100A, L_s = 30nH, V_{GE} = +15/-15 V, R_G = 27 Ω	T_{Vj}=25°C	-	0.39	-	
				T_{Vj}=125°C	-	0.60	-	
				T_{Vj}=150°C	-	0.70	-	
				T_{Vj}=175°C	-	0.81	-	
Brake	Zero Gate voltage collector current	I_{CES}	V_{GE} = 0V, V_{CE} = 650V		-	-	50	μA
	Gate-Emitter leakage current	I_{GES}	V_{CE} = 0V, V_{GE} = +20/-20V		-	-	100	nA
	Collector-Emitter saturation voltage	$V_{CE(sat)}$ (terminal)	V_{GE} = 15V, I_C = 50A	T_{Vj}=25°C	-	1.45	1.90	V
		$V_{CE(sat)}$ (chip)		T_{Vj}=25°C	-	1.30	1.75	
				T_{Vj}=125°C	-	1.45	-	
				T_{Vj}=150°C	-	1.50	-	
				T_{Vj}=175°C	-	1.55	-	
	Internal Gate resistance	r_g	-		-	0	-	Ω
	Switching time (*1)	$t_{d(on)}$	V_{CC} = 300V, I_C = 50A, L_s = 30nH, V_{GE} = +15/-15 V, R_G = 68 Ω	T_{Vj}=25°C	-	0.35	-	μs
				T_{Vj}=125°C	-	0.36	-	
				T_{Vj}=150°C	-	0.36	-	
				T_{Vj}=175°C	-	0.35	-	
		t_r	V_{CC} = 300V, I_C = 50A, L_s = 30nH, V_{GE} = +15/-15 V, R_G = 68 Ω	T_{Vj}=25°C	-	0.10	-	
				T_{Vj}=125°C	-	0.13	-	
				T_{Vj}=150°C	-	0.14	-	
				T_{Vj}=175°C	-	0.14	-	
		$t_{d(off)}$	V_{CC} = 300V, I_C = 50A, L_s = 30nH, V_{GE} = +15/-15 V, R_G = 68 Ω	T_{Vj}=25°C	-	0.52	-	
				T_{Vj}=125°C	-	0.50	-	
				T_{Vj}=150°C	-	0.55	-	
				T_{Vj}=175°C	-	0.56	-	
		t_f	V_{CC} = 300V, I_C = 50A, L_s = 30nH, V_{GE} = +15/-15 V, R_G = 68 Ω	T_{Vj}=25°C	-	0.04	-	
				T_{Vj}=125°C	-	0.04	-	
				T_{Vj}=150°C	-	0.04	-	
				T_{Vj}=175°C	-	0.04	-	
	Reverse current	I_{RRM}	V_R = 650V		-	-	50	μA
	Forward voltage	V_F (terminal)	I_F = 30A	T_{Vj}=25°C	-	1.70	2.15	V
		V_F (chip)	I_F = 30A	T_{Vj}=25°C	-	1.55	2.00	
				T_{Vj}=125°C	-	1.50	-	
				T_{Vj}=150°C	-	1.50	-	
				T_{Vj}=175°C	-	1.45	-	
Converter	Reverse current	I_{RRM}	V_R = 800V		-	-	50	μA
	Forward voltage	V_{FM}	I_F = 100A	terminal	-	1.35	1.85	V
				chip	-	1.10	1.55	
Thermistor	Resistance	R	T = 25°C		-	5000	-	Ω
			T = 100°C		465	495	520	
	B value	B	T = 25/ 50°C		3305	3375	3450	K

(*1) Turn on time (t_{on}) = $t_{d(on)}$ + t_r , Turn off time (t_{off}) = $t_{d(off)}$ + t_f

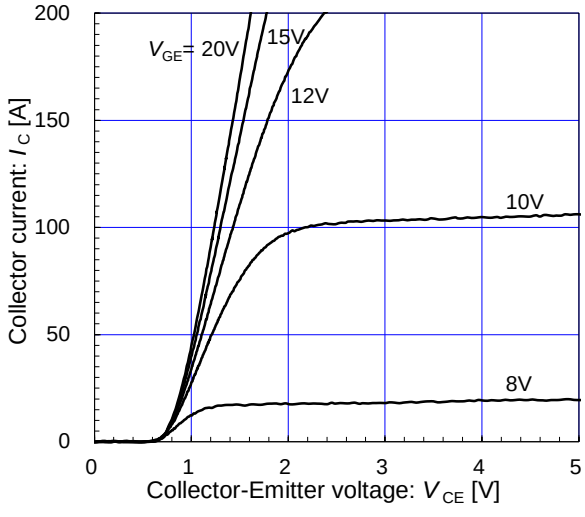
NOTICE:
The external gate resistance (R_G) shown above is one of our recommended value for the purpose of minimum switching loss. However the optimum R_G depends on circuit configuration and/or environment. We recommend that the R_G has to be carefully chosen based on consideration if IGBT module matches design criteria, for example, switching loss, EMC/EMI, spike voltage, surge current and no unexpected oscillation and so on.

□Thermal resistance characteristics

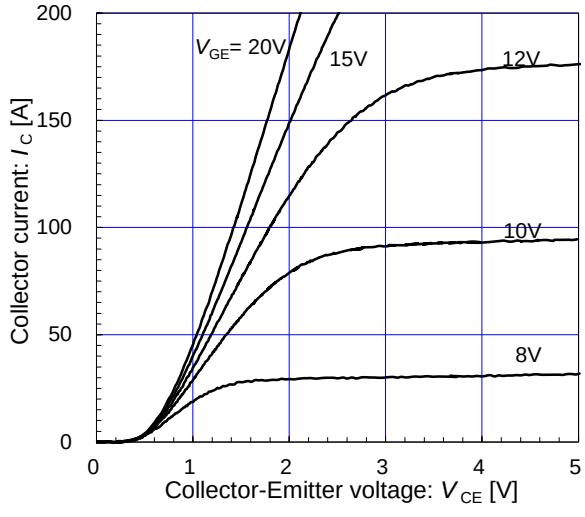
Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	max.	
Thermal resistance (1device)	$R_{th(j-c)}$	Inverter IGBT	-	-	0.45	°C/W
		Inverter FWD	-	-	0.58	
		Brake IGBT	-	-	0.71	
		Brake FWD	-	-	1.21	
		Converter Diode	-	-	0.48	
Contact thermal resistance (1 IGBT+1 FWD) (*1)	$R_{th(c-f)}$	with 1 W/(m·K) thermal grease	-	0.05	-	

(*1) This is the value which is defined mounting on the additional cooling fin with thermal grease.

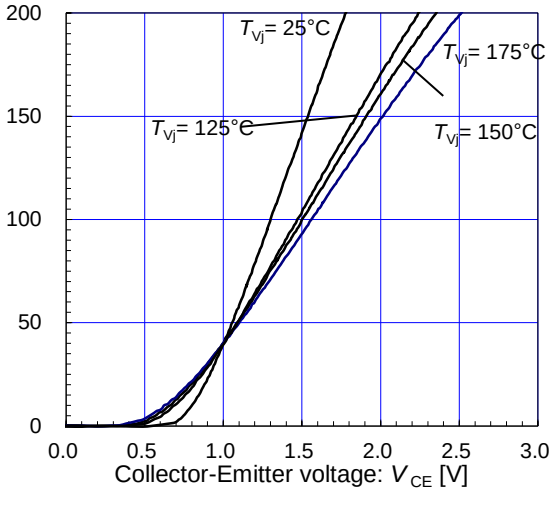
[Inverter]
Collector current vs. Collector-Emitter voltage (typ.)
T_{Vj}= 25°C / chip



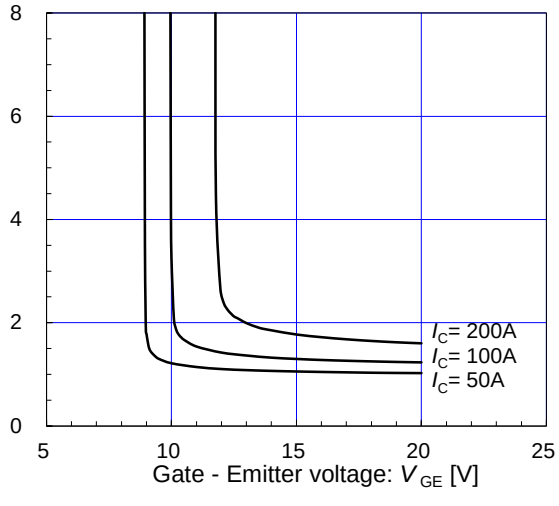
[Inverter]
Collector current vs. Collector-Emitter voltage (typ.)
T_{Vj}= 175°C / chip



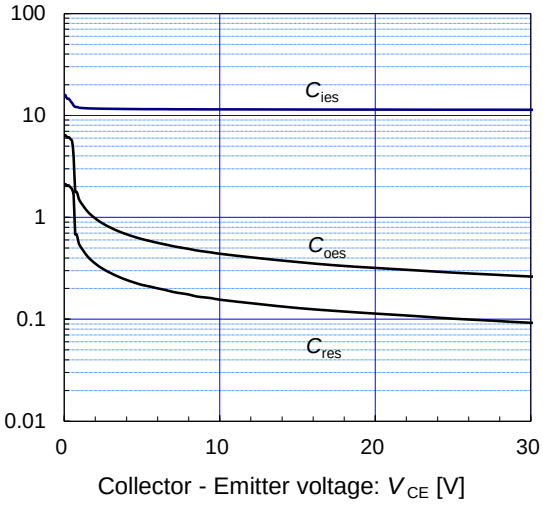
[Inverter]
Collector current vs. Collector-Emitter voltage (typ.)
V_{GE}=15V / chip



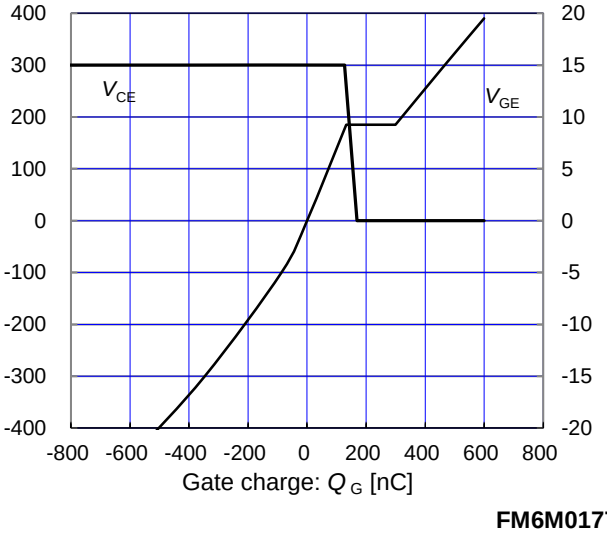
[Inverter]
Collector-Emitter voltage vs. Gate-Emitter voltage (typ.)
T_{Vj}= 25°C / chip



[Inverter]
Capacitance vs. Collector-Emitter voltage (typ.)
V_{GE}=0V, f= 1MHz, T_{Vj}= 25°C



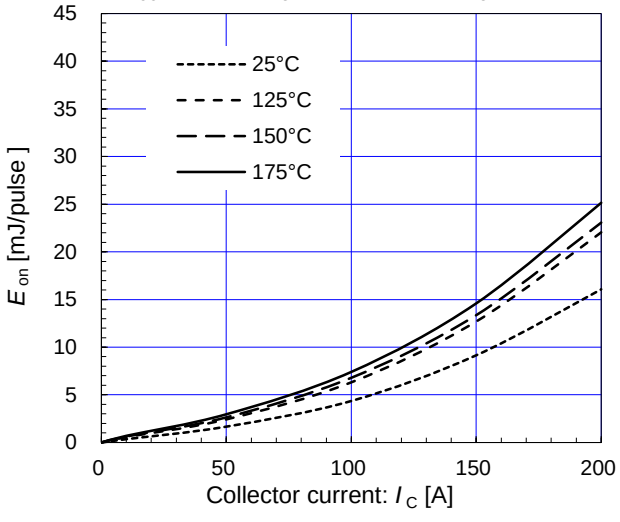
[Inverter]
Dynamic Gate charge (typ.)
V_{CC}= 300V, I_C= 100A, T_{Vj}= 25°C



[Inverter]

E_{on} vs. Collector current (typ.)

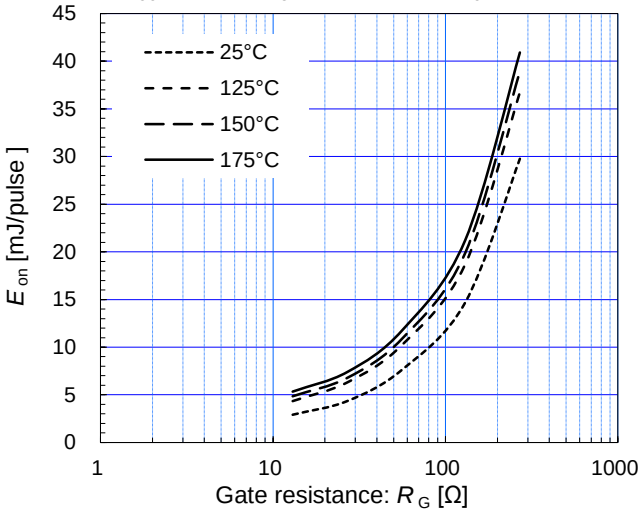
V_{CC}= 300V, V_{GE}= +15/-15 V, R_G= 27 Ω



[Inverter]

E_{on} vs. Gate resistance (typ.)

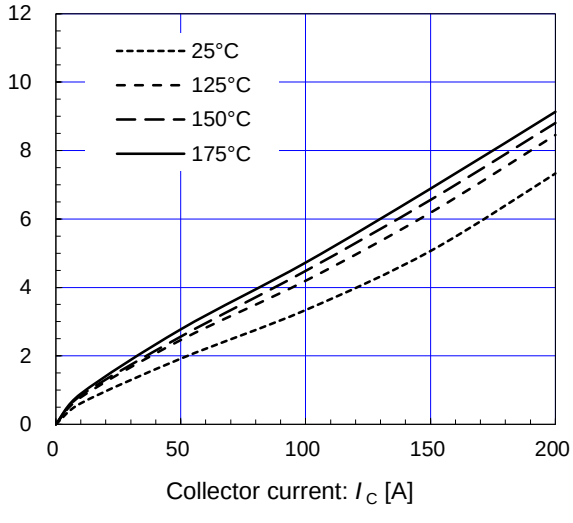
V_{CC}= 300V, V_{GE}= +15/-15 V, I_C= 100A



[Inverter]

E_{off} vs. Collector current (typ.)

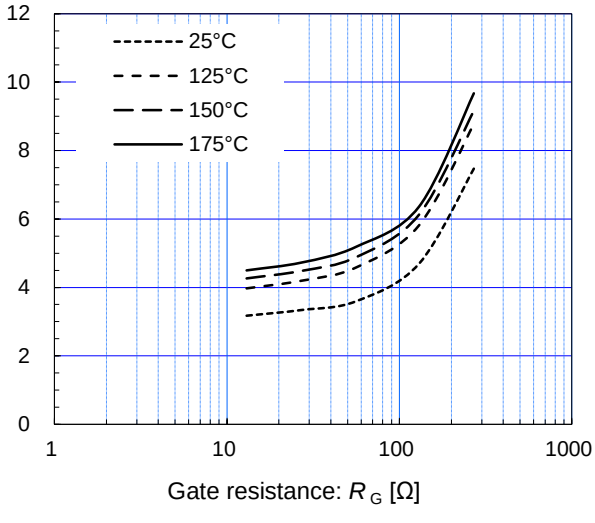
V_{CC}= 300V, V_{GE}= +15/-15 V, R_G= 27 Ω



[Inverter]

E_{off} vs. Gate resistance (typ.)

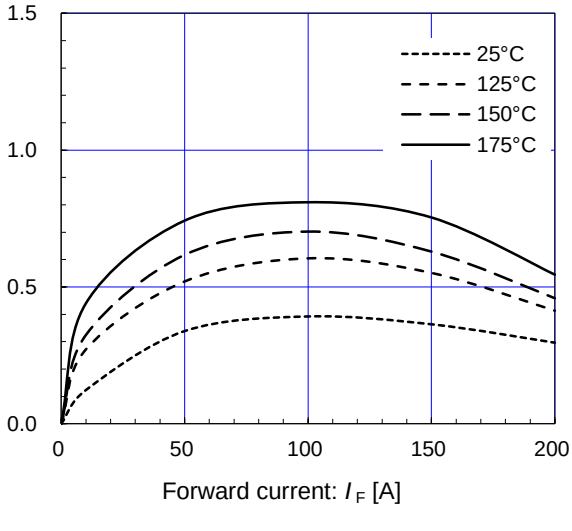
V_{CC}= 300V, V_{GE}= +15/-15 V, I_C= 100A



[Inverter]

E_{rr} vs. Forward current (typ.)

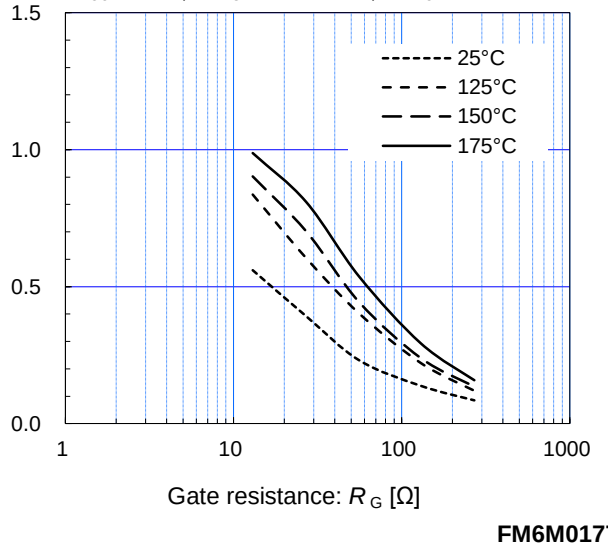
V_{CC}= 300V, V_{GE}= +15/-15 V, R_G= 27 Ω



[Inverter]

E_{rr} vs. Gate resistance (typ.)

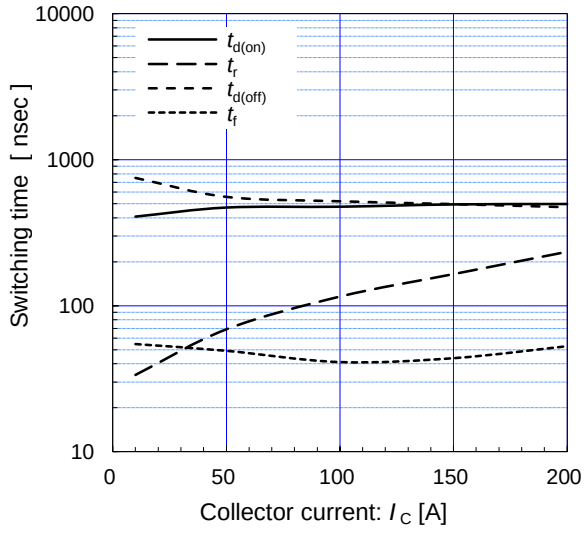
V_{CC}= 300V, V_{GE}= +15/-15 V, I_C= 100A



[Inverter]

Switching time vs. Collector current (typ.)

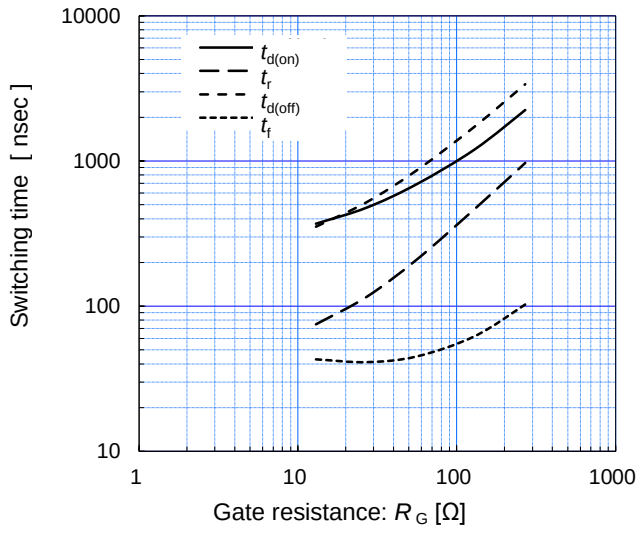
V_{CC}= 300V, R_G= 27Ω V_{GE}= +15/-15 V, T_{Vj}= 25°C



[Inverter]

Switching time vs. Gate resistance (typ.)

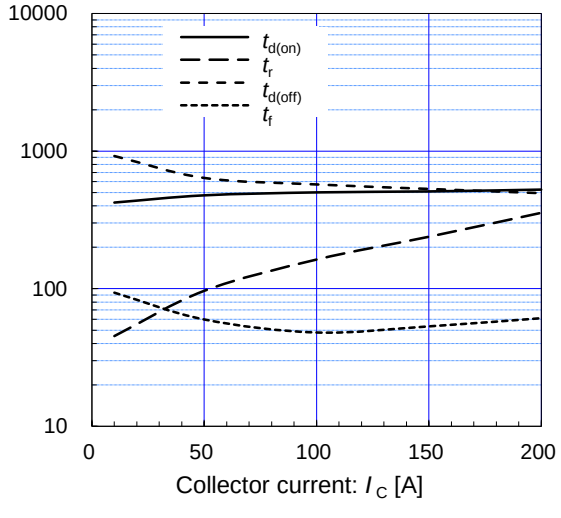
V_{CC}= 300V, I_C= 100A, V_{GE}= +15/-15 V, T_{Vj}= 25°C



[Inverter]

Switching time vs. Collector current (typ.)

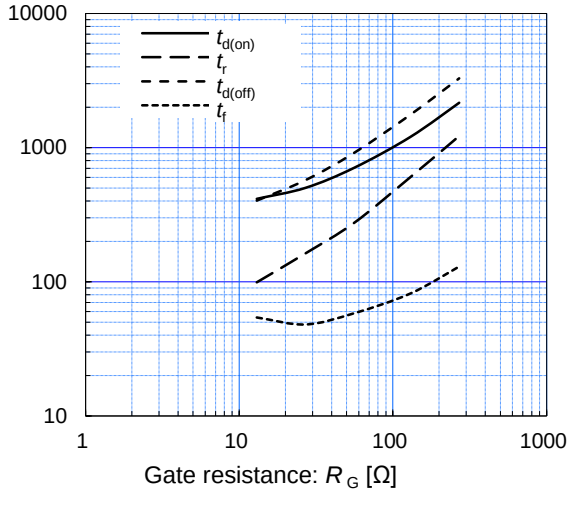
V_{CC}= 300V, R_G= 27Ω V_{GE}= +15/-15 V, T_{Vj}= 175°C



[Inverter]

Switching time vs. Gate resistance (typ.)

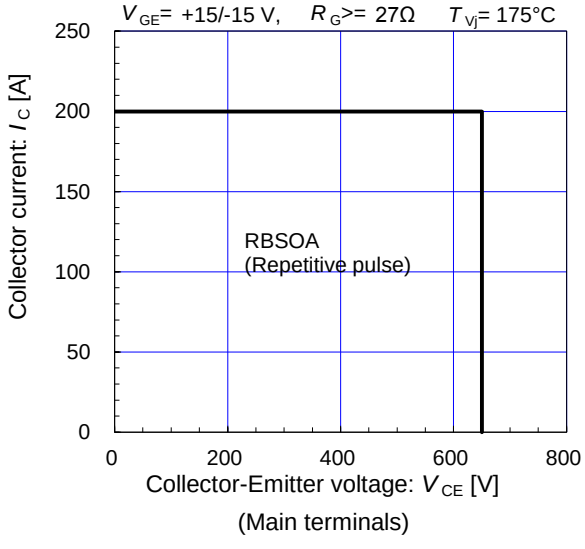
V_{CC}= 300V, I_C= 100A, V_{GE}= +15/-15 V, T_{Vj}= 175°C



[Inverter]

Reverse bias safe operating area (max.)

V_{GE}= +15/-15 V, R_G>= 27Ω T_{Vj}= 175°C

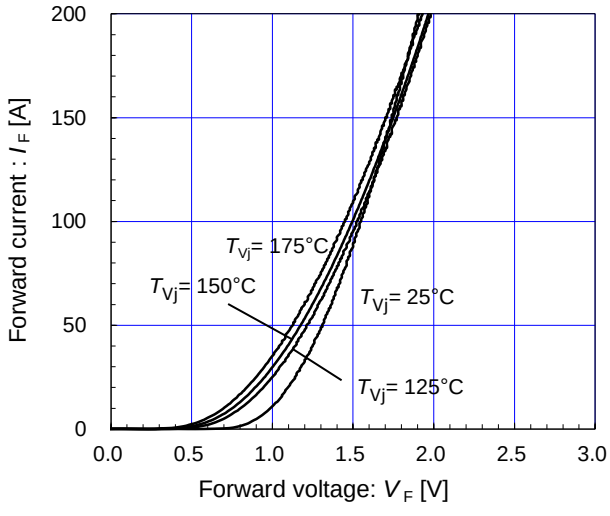


(Main terminals)

[Inverter]

Forward current vs. Forward voltage (typ.)

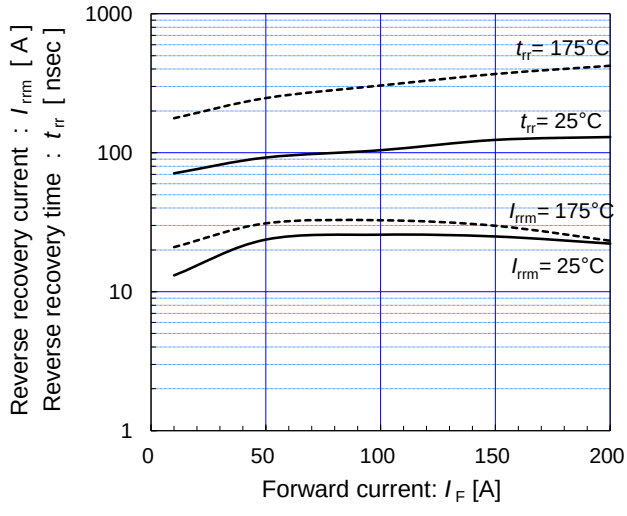
chip



[Inverter]

Reverse recovery characteristics (typ.)

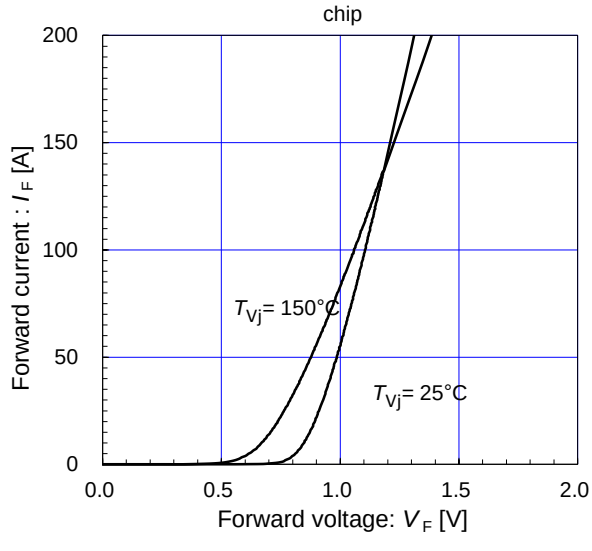
V_{CC}= 300V, V_{GE}= +15/-15 V, R_G= 27Ω



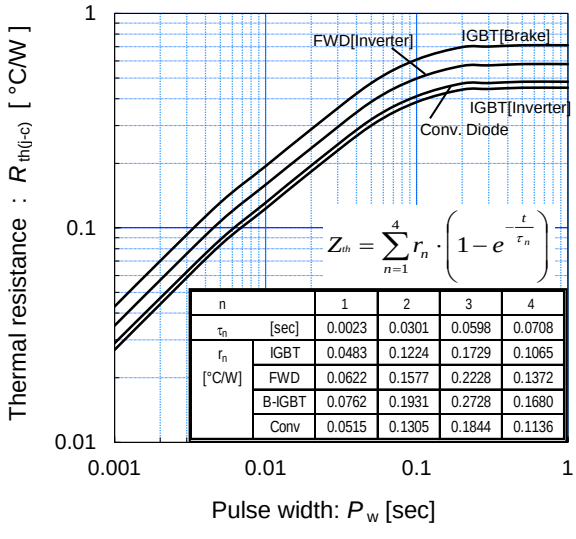
[Converter]

Forward current vs. Forward voltage (typ.)

chip



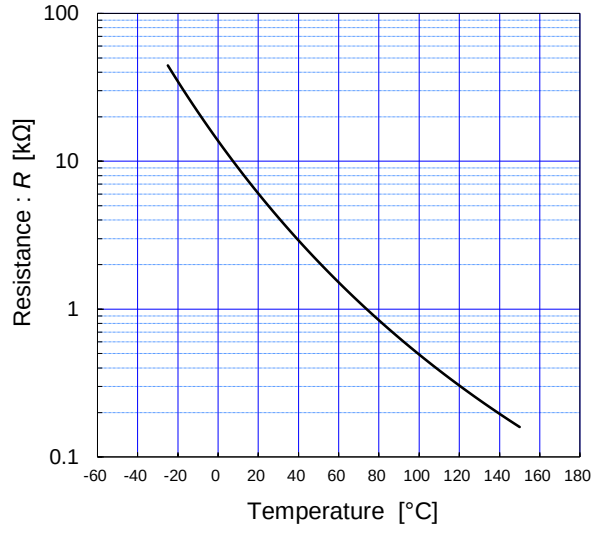
Transient thermal resistance (max.)



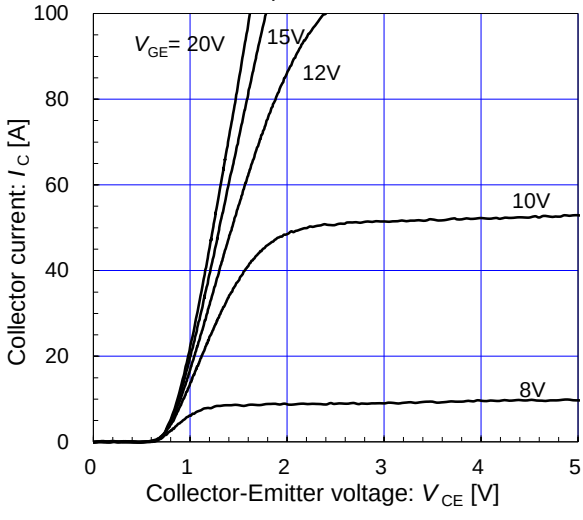
n		1	2	3	4
τ_n	[sec]	0.0023	0.0301	0.0598	0.0708
r_n [°C/W]	IGBT	0.0483	0.1224	0.1729	0.1065
	FWD	0.0622	0.1577	0.2228	0.1372
	B-IGBT	0.0762	0.1931	0.2728	0.1680
	Conv	0.0515	0.1305	0.1844	0.1136

[Thermistor]

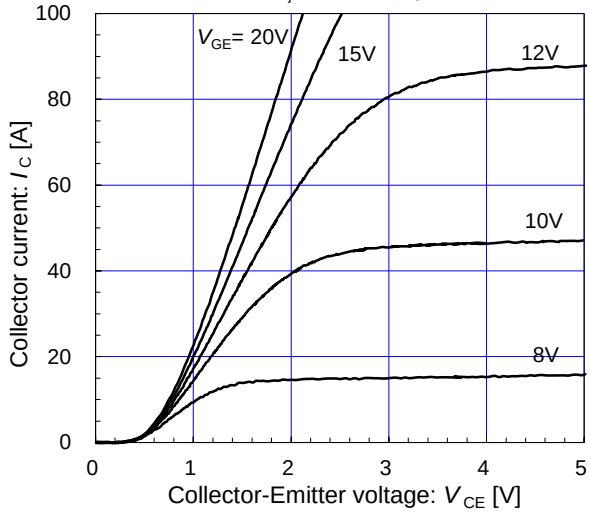
Temperature characteristic (typ.)



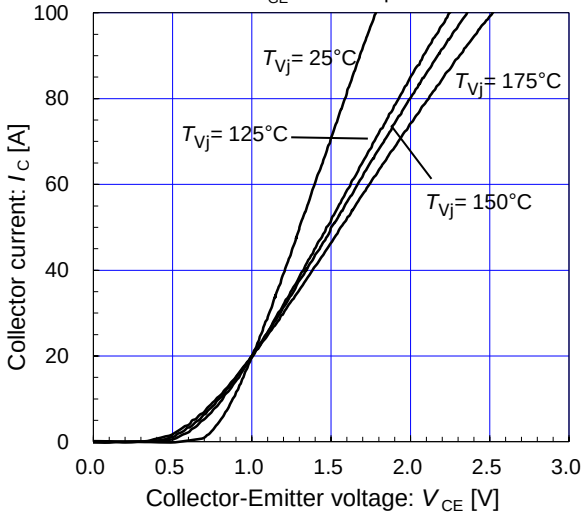
[Brake]
Collector current vs. Collector-Emitter voltage (typ.)
T_{Vj}= 25°C / chip



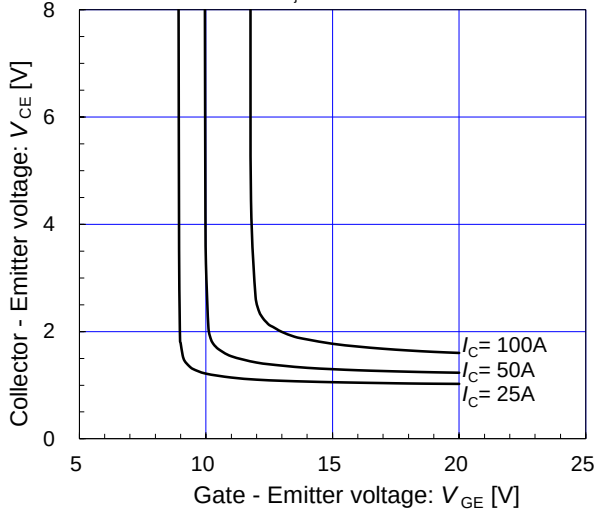
[Brake]
Collector current vs. Collector-Emitter voltage (typ.)
T_{Vj}= 175°C / chip



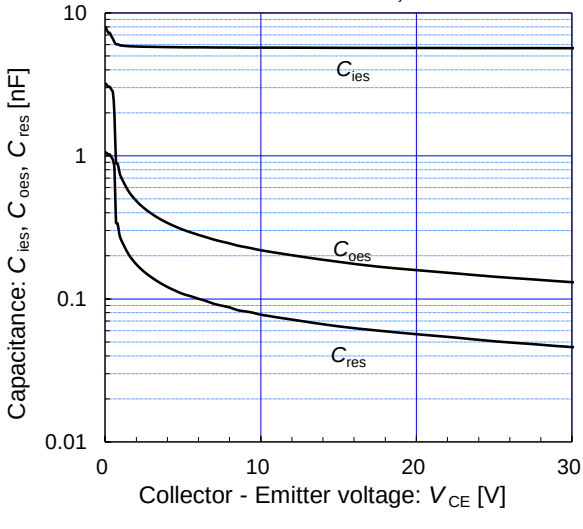
[Brake]
Collector current vs. Collector-Emitter voltage (typ.)
V_{GE}=15V / chip



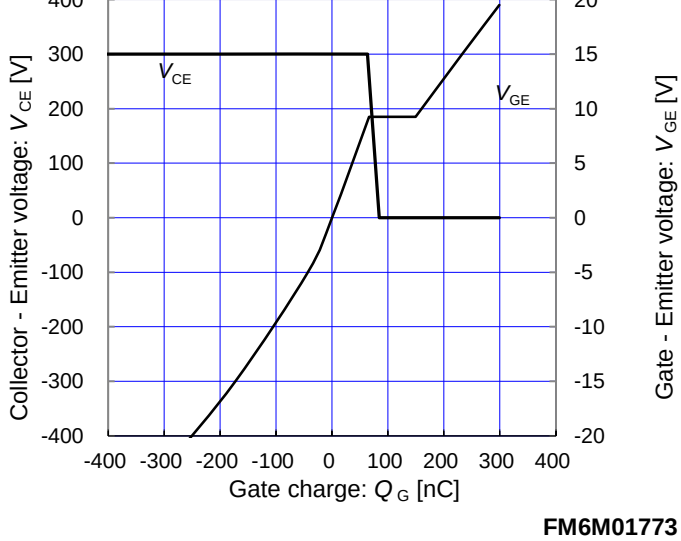
[Brake]
Collector-Emitter voltage vs. Gate-Emitter voltage (typ.)
T_{Vj}= 25°C / chip



[Brake]
Capacitance vs. Collector-Emitter voltage (typ.)
V_{GE}=0V, f= 1MHz, T_{Vj}= 25°C



[Brake]
Dynamic Gate charge (typ.)
V_{CC}= 300V, I_C= 50A, T_{Vj}= 25°C



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・Emergency equipment for responding to disasters and anti-burglary devices ・Safety devices ・Medical equipment

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7.

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